

Appl. No. 10/717,731  
Response dated July 28, 2005  
Reply to Office action dated Jun. 29, 2005

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of claims:**

1-15. (canceled)

16. (currently amended) A ~~semiconductor die assembled into a packaged~~ semiconductor device ~~by a method~~ comprising:

a semiconductor die;

~~dispensing a die attach material onto~~ a chip carrier;

~~, wherein the~~ a die attach material comprises including a component of which the CTE is negative negative-CTE material; and

~~attaching a~~ the semiconductor die attached to the chip carrier with ~~[[to]]~~ the die attach material.

17. (currently amended) The semiconductor ~~[[die]]~~ device of claim 16, wherein ~~dispensing the die attach material onto the chip carrier further comprises dispensing the die attach material onto a structure~~ is selected from a group consisting of a package substrate and a leadframe.

18. (currently amended) The semiconductor ~~[[die]]~~ device of claim ~~[[17]]~~ 16, wherein ~~dispensing a die attach material comprising a the component with negative-CTE material further comprises dispensing a die attach material comprising a~~ is a tungstate material.

19. (original) The semiconductor ~~[[die]]~~ device of claim 16, ~~wherein the method further comprises encapsulating the semiconductor die with~~ further comprising an encapsulant that

TI-36243 - 2

Appl. No. 10/717,731  
Response dated July 28, 2005  
Reply to Office action dated Jun. 29, 2005

encapsulates the semiconductor die, the encapsulant including a component of comprising a negative-CTE material.

20. (currently amended) The semiconductor ~~[[die]]~~ device of claim 19, wherein ~~encapsulating the semiconductor die with an encapsulant comprising a negative-CTE material further comprises encapsulating the semiconductor die with an encapsulant comprising a~~ the encapsulant includes a tungstate material.

21. (currently amended) The semiconductor ~~[[die]]~~ device of claim 19, wherein ~~encapsulating the semiconductor die with an~~ the encapsulant further comprises encapsulating the semiconductor die with a material is selected from a group consisting of a mold compound and a glob-top material.

22. (currently amended) A semiconductor ~~die assembled into a packaged semiconductor device by a method~~ comprising:

a semiconductor die disposed on a chip carrier;

dispensing a lid attach material comprising a negative-CTE material disposed over the

inactive a surface of a semiconductor die and around at least a portion of a

perimeter of the upper surface of a package substrate the chip carrier; and

adhering a package a lid adhered to the lid attach material.

23. (currently amended) The ~~method~~ semiconductor device of claim 22, wherein ~~[[dispensing]] the lid attach material comprising a negative-CTE material further comprises dispensing a lid attach material comprising~~ includes a tungstate material.

Appl. No. 10/717,731

Response dated July 28, 2005

Reply to Office action dated Jun. 29, 2005

24. (currently amended) The ~~method~~ semiconductor device of claim 23, wherein ~~dispensing the lid attach material comprising a~~ the tungstate material further comprises dispensing a lid attach material comprising a material is selected from a group consisting of zirconium tungstate, hafnium tungstate, and a solution of zirconium and hafnium tungstate.
25. (new) The semiconductor of claim 19, in which the die attaching material and the encapsulant include a component selected from a group consisting of zirconium tungstate, hafnium tungstate, and a solution of zirconium and hafnium tungstate.